

Ganesh Balakrishnan

List of Publications by Year in descending order

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198
papers

3,093
citations

147726

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h-index

197736

49
g-index

199
all docs

199
docs citations

199
times ranked

2715
citing authors

#	ARTICLE	IF	CITATIONS
1	Strain relief by periodic misfit arrays for low defect density GaSb on GaAs. Applied Physics Letters, 2006, 88, 131911.	1.5	238
2	Light-Emitting Metasurfaces: Simultaneous Control of Spontaneous Emission and Far-Field Radiation. Nano Letters, 2018, 18, 6906-6914.	4.5	126
3	Optically Pumped Frequency Reconfigurable Antenna Design. IEEE Antennas and Wireless Propagation Letters, 2010, 9, 280-283.	2.4	107
4	Demonstration of a Cognitive Radio Front End Using an Optically Pumped Reconfigurable Antenna System (OPRAS). IEEE Transactions on Antennas and Propagation, 2012, 60, 1075-1083.	3.1	93
5	III/V ratio based selectivity between strained Stranski-Krastanov and strain-free GaSb quantum dots on GaAs. Applied Physics Letters, 2006, 89, 161104.	1.5	89
6	Interfacial misfit array formation for GaSb growth on GaAs. Journal of Applied Physics, 2009, 105, .	1.1	87
7	2.0 μ m wavelength InAs quantum dashes grown on a GaAs substrate using a metamorphic buffer layer. Applied Physics Letters, 2004, 84, 2058-2060.	1.5	80
8	Effect of dislocation density on thermal boundary conductance across GaSb/GaAs interfaces. Applied Physics Letters, 2011, 98, .	1.5	73
9	Growth mechanisms of highly mismatched AlSb on a Si substrate. Applied Physics Letters, 2005, 86, 034105.	1.5	72
10	Atomistic modeling of strain distribution in self-assembled interfacial misfit dislocation (IMF) arrays in highly mismatched III-V semiconductor materials. Journal of Crystal Growth, 2007, 303, 449-455.	0.7	67
11	Self-Organized Formation of GaSb/GaAs Quantum Rings. Physical Review Letters, 2008, 101, 256101.		67
12	Single-mode lasing of GaN nanowire-pairs. Applied Physics Letters, 2012, 101, .	1.5	63
13	Simultaneous interfacial misfit array formation and antiphase domain suppression on miscut silicon substrate. Applied Physics Letters, 2008, 93, .	1.5	61
14	Mid-infrared InAs/GaSb strained layer superlattice detectors with nBn design grown on a GaAs substrate. Semiconductor Science and Technology, 2010, 25, 085010.	1.0	56
15	Lasing characteristics of GaSb/GaAs self-assembled quantum dots embedded in an InGaAs quantum well. Applied Physics Letters, 2007, 90, 261115.	1.5	54
16	Formation and optical characteristics of strain-relieved and densely stacked GaSb/GaAs quantum dots. Applied Physics Letters, 2006, 89, 203116.	1.5	53
17	Controlled InAs quantum dot nucleation on faceted nanopatterned pyramids. Applied Physics Letters, 2007, 90, 183103.	1.5	50
18	Structural Analysis of Highly Relaxed GaSb Grown on GaAs Substrates with Periodic Interfacial Array of 90 $^\circ$ Misfit Dislocations. Nanoscale Research Letters, 2009, 4, 1458-62.	3.1	50

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19	Quantum ring formation and antimony segregation in GaSb-GaAs nanostructures. Journal of Vacuum Science & Technology B, 2008, 26, 1492-1503.	1.3	48
20	Interplay between total thickness and period thickness in the phonon thermal conductivity of superlattices from the nanoscale to the microscale: Coherent versus incoherent phonon transport. Physical Review B, 2018, 97, .	1.1	48
21	Selective area growth of InAs quantum dots formed on a patterned GaAs substrate. Applied Physics Letters, 2004, 85, 2337-2339.	1.5	45
22	Fabrication of Self-Aligned Enhancement-Mode $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOSFETs With $\text{TaN}/\text{HfO}_2/\text{AlN}$ Gate Stack. IEEE Electron Device Letters, 2008, 29, 557-560.	2.2	43
23	Room-Temperature Optically Pumped (Al)GaSb Vertical-Cavity Surface-Emitting Laser Monolithically Grown on an Si(1 0 0) Substrate. IEEE Journal of Selected Topics in Quantum Electronics, 2006, 12, 1636-1641.	1.9	41
24	Gallium free type II InAs/InAsSb $_{1-x}$ superlattice photodetectors. Applied Physics Letters, 2012, 101, 071111.	1.5	40
25	Epitaxial growth and formation of interfacial misfit array for tensile GaAs on GaSb. Applied Physics Letters, 2007, 90, 161902.	1.5	39
26	Temperature dependent carrier dynamics in telecommunication band InAs quantum dots and dashes grown on InP substrates. Journal of Applied Physics, 2013, 113, .	1.1	37
27	GaSb quantum-well-based ϵ -buffer-free vertical light emitting diode monolithically embedded within a GaAs cavity incorporating interfacial misfit arrays. Applied Physics Letters, 2006, 89, 211110.	1.5	34
28	Room-Temperature Operation of Buffer-Free GaSb-AlGaSb Quantum-Well Diode Lasers Grown on a GaAs Platform Emitting at 1.65 μm . IEEE Photonics Technology Letters, 2007, 19, 1628-1630.	1.3	33
29	Tabletop single-shot extreme ultraviolet Fourier transform holography of an extended object. Optics Express, 2013, 21, 9959.	1.7	33
30	Room-temperature optically-pumped GaSb quantum well based VCSEL monolithically grown on Si (100) substrate. Electronics Letters, 2006, 42, 350.	0.5	32
31	Gold substrate-induced single-mode lasing of GaN nanowires. Applied Physics Letters, 2012, 101, 221114.	1.5	32
32	1.54 μm GaSb/AlGaSb multi-quantum-well monolithic laser at 77 K grown on miscut Si substrate using interfacial misfit arrays. Electronics Letters, 2007, 43, 1198.	0.5	30
33	Single dot spectroscopy of site-controlled InAs quantum dots nucleated on GaAs nanopillars. Applied Physics Letters, 2007, 91, 133104.	1.5	27
34	Vertical carrier transport in strain-balanced InAs/InAsSb type-II superlattice material. Applied Physics Letters, 2020, 116, .	1.5	27
35	WEST: Cloning data cache behavior using Stochastic Traces. , 2012, , .		25
36	Controlled Growth of Ordered III-Nitride Core-Shell Nanostructure Arrays for Visible Optoelectronic Devices. Journal of Electronic Materials, 2015, 44, 1255-1262.	1.0	25

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37	Time-resolved photoluminescence of type-II Ga(As)Sb/GaAs quantum dots embedded in an InGaAs quantum well. <i>Nanotechnology</i> , 2008, 19, 295704.	1.3	24
38	Thermal plasmons controlled by different thermal-convolution paths in tunable extrinsic Dirac structures. <i>Physical Review B</i> , 2017, 96, .	1.1	24
39	Room-temperature lasing at 1.82 μ m of GaInSb δ -AlGaSb quantum wells grown on GaAs substrates using an interfacial misfit array. <i>Applied Physics Letters</i> , 2007, 91, 141102.	1.5	23
40	Monolithically Integrated III-Sb-Based Laser Diodes Grown on Miscut Si Substrates. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009, 15, 716-723.	1.9	23
41	Modeling and experimental realization of modelocked VECSEL producing high power sub-100 fs pulses. <i>Applied Physics Letters</i> , 2018, 113, .	1.5	23
42	Room-temperature optically-pumped InGaSb quantum well lasers monolithically grown on Si(100) substrate. <i>Electronics Letters</i> , 2005, 41, 531.	0.5	22
43	GaSb Thermophotovoltaic Cells Grown on GaAs Substrate Using the Interfacial Misfit Array Method. <i>Journal of Electronic Materials</i> , 2014, 43, 902-908.	1.0	22
44	Coulomb effects in type-II Ga(As)Sb quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 752-755.	0.7	21
45	Temperature dependence of GaSb and AlGaSb solar cells. <i>Current Applied Physics</i> , 2018, 18, 752-761.	1.1	20
46	Optical properties of patterned InAs quantum dot ensembles grown on GaAs nanopillars. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	19
47	Epitaxial growth of cerium oxide thin films by pulsed laser deposition. <i>Thin Solid Films</i> , 2013, 546, 467-471.	0.8	19
48	Multi-watt 1.25 μ m quantum dot VECSEL. <i>Electronics Letters</i> , 2010, 46, 856.	0.5	18
49	Green synthesis of zinc oxysulfide quantum dots using aegle marmelos fruit extract and their cytotoxicity in HeLa cells. <i>RSC Advances</i> , 2015, 5, 16815-16820.	1.7	18
50	Understanding the visual skills and strategies of train drivers in the urban rail environment. <i>Work</i> , 2014, 47, 339-352.	0.6	17
51	Semipolar InGaN/GaN nanostructure light-emitting diodes on c-plane sapphire. <i>Applied Physics Express</i> , 2016, 9, 032101.	1.1	17
52	Optical transition pathways in type-II Ga(As)Sb quantum dots. <i>Journal of Luminescence</i> , 2009, 129, 456-460.	1.5	16
53	Going solo: Hierarchical task analysis of the second driver in a two-up (multi-person) freight rail operations. <i>Applied Ergonomics</i> , 2018, 70, 202-231.	1.7	16
54	Electrical and microstructure analysis of nickel-based low-resistance ohmic contacts to n-GaSb. <i>APL Materials</i> , 2013, 1, .	2.2	15

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55	Polarization switching in GaN nanowire lasers. Applied Physics Letters, 2013, 103, .	1.5	15
56	340-W Peak Power From a GaSb 2- μm Optically Pumped Semiconductor Laser (OPSL) Grown Mismatched on GaAs. IEEE Photonics Technology Letters, 2010, 22, 1253-1255.	1.3	14
57	Polarization control in GaN nanowire lasers. Optics Express, 2014, 22, 19198.	1.7	14
58	Reduction of reverse leakage current in selective area-grown GaN-based core-shell nanostructure LEDs using AlGaIn layers. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600776.	0.8	14
59	InP-Based Waveguide-Integrated Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells and 10-GHz Bandwidth at 2 μm Wavelength. Journal of Lightwave Technology, 2018, 36, 4981-4987.	2.7	14
60	Implementation of a cognitive radio front-end using optically reconfigurable antennas. , 2010, , .		13
61	Recording oscillations of sub-micron size cantilevers by extreme ultraviolet Fourier transform holography. Optics Express, 2014, 22, 4161.	1.7	13
62	Multi-Angle VECSEL Cavities for Dispersion Control and Peak-Power Scaling. IEEE Photonics Technology Letters, 2017, 29, 326-329.	1.3	13
63	Reducing threading dislocation density in GaSb photovoltaic devices on GaAs by using AlSb dislocation filtering layers. Solar Energy Materials and Solar Cells, 2018, 185, 21-27.	3.0	13
64	Temperature-Dependent Minority-Carrier Mobility in $\text{In}_{0.5}\text{Ga}_{0.5}\text{Sb}$ Type-II Quantum Wells. Applied Physics Letters, 2010, 96, 072109.	1.5	13
65	Compensation of interfacial states located inside the $\text{In}_{0.5}\text{Ga}_{0.5}\text{Sb}/\text{GaAs}$ (001) heterojunction via In -doping. Applied Physics Letters, 2009, 95, 072109.	1.5	12
66	Influence of background gas atmosphere on formation of Cr_2O_3 thin films prepared by pulsed laser deposition. Surface Engineering, 2009, 25, 223-227.	1.1	12
67	Epitaxial Regrowth and Hole Shape Engineering for Photonic Crystal Surface Emitting Lasers (PCSELs). Journal of Crystal Growth, 2020, 535, 125531.	0.7	12
68	High quality AlSb bulk material on Si substrates using a monolithic self-assembled quantum dot nucleation layer. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1010.	1.6	11
69	Record pulsed power demonstration of a $2\frac{1}{4}\mu\text{m}$ GaSb-based optically pumped semiconductor laser grown lattice-mismatched on an AlAs/GaAs Bragg mirror and substrate. Applied Physics Letters, 2009, 95, 081112.	1.5	11
70	Transmission Electron Microscopy-Based Analysis of Electrically Conductive Surface Defects in Large Area GaSb Homoepitaxial Diodes Grown Using Molecular Beam Epitaxy. Journal of Electronic Materials, 2014, 43, 926-930.	1.0	11
71	High-Speed InP-Based p-i-n Photodiodes With InGaAs/GaAsSb Type-II Quantum Wells. IEEE Photonics Technology Letters, 2018, 30, 399-402.	1.3	11
72	Scaling Challenges in High Power Photonic Crystal Surface-Emitting Lasers. IEEE Journal of Quantum Electronics, 2022, 58, 1-9.	1.0	11

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73	Continuous-Wave, Room-Temperature Operation of 2- μm Sb-Based Optically-Pumped Vertical-External-Cavity Surface-Emitting Laser Monolithically Grown on GaAs Substrates. Applied Physics Express, 2009, 2, 112102.	1.1	10
74	Growth Mode and Defect Evaluation of GaSb on GaAs Substrate: A Transmission Electron Microscopy Study. Journal of Nanoscience and Nanotechnology, 2011, 11, 5108-5113.	0.9	10
75	1220-1280-nm Optically Pumped InAs Quantum Dot-Based Vertical External-Cavity Surface-Emitting Laser. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1787-1793.	1.9	10
76	InAs FinFETs Performance Enhancement by Superacid Surface Treatment. IEEE Transactions on Electron Devices, 2019, 66, 1856-1861.	1.6	10
77	Onset of GaSb/GaAs quantum dot formation. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3971-3974.	0.8	9
78	Room temperature InGaSb quantum well microcylinder lasers at 2- μm grown monolithically on a silicon substrate. Journal of Vacuum Science & Technology B, 2007, 25, 1622.	1.3	9
79	Electronic characteristics of the interfacial states embedded in $\text{InAs}/\text{GaSb}/\text{GaAs}$ (001) heterojunctions. Applied Physics Letters, 2009, 95, 202107.	1.5	9
80	Optically pumped reconfigurable antenna systems (OPRAS)., 2010, , .		9
81	Relaxation dynamics and residual strain in metamorphic AlSb on GaAs. Applied Physics Letters, 2012, 100, .	1.5	9
82	High power 1.25- μm InAs quantum dot vertical external-cavity surface-emitting laser. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, .	0.6	8
83	Three-dimensional GaN templates for molecular beam epitaxy of nonpolar InGaN/GaN coaxial light-emitting diodes. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 03C107.	0.6	8
84	AlGaSb-Based Solar Cells Grown on GaAs: Structural Investigation and Device Performance. IEEE Journal of Photovoltaics, 2017, 7, 1795-1801.	1.5	8
85	Interfacial misfit dislocation array based growth of III-Sb active regions on GaAs/AlGaAs DBRs for high-power 2- μm VECSELs. Proceedings of SPIE, 2008, , .	0.8	7
86	Formation and Optical Characteristics of Type-II Strain-Relieved GaSb/GaAs Quantum Dots by Using an Interfacial Misfit Growth Mode. IEEE Nanotechnology Magazine, 2009, 8, 269-274.	1.1	7
87	Growth and thermal conductivity analysis of polycrystalline GaAs on chemical vapor deposition diamond for use in thermal management of high-power semiconductor lasers. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 03C130.	0.6	7
88	Intrinsic localized modes in two-dimensional vibrations of crystalline pillars and their application for sensing. Journal of Applied Physics, 2012, 112, .	1.1	7
89	MeToo: Stochastic Modeling of Memory Traffic Timing Behavior. , 2015, , .		7
90	Wavelength beam combining of VECSELs using multiplexed volume Bragg gratings in a compound cavity. Electronics Letters, 2015, 51, 508-510.	0.5	7

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91	High-Resistivity Semi-insulating AlSb on GaAs Substrates Grown by Molecular Beam Epitaxy. Journal of Electronic Materials, 2016, 45, 2025-2030.	1.0	7
92	Active Mediation of Plasmon Enhanced Localized Exciton Generation, Carrier Diffusion and Enhanced Photon Emission. Scientific Reports, 2017, 7, 864.	1.6	7
93	Analysis of atomic structure in InAs quantum dashes grown on AlGaAsSb metamorphic buffers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1529.	1.6	6
94	Monolithically integrated III-Sb CW super-luminal light emitting diodes on non-miscut Si (100) substrates. Electronics Letters, 2007, 43, 244.	0.5	6
95	Influence of non-radiative carrier losses on pulsed and continuous VECSEL performance. , 2012, , .		6
96	Ohmic contacts to n-type GaSb grown on GaAs by the interfacial misfit dislocation technique. Proceedings of SPIE, 2013, , .	0.8	6
97	Characterization of surface defects on Be-implanted GaSb. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 04E109.	0.6	6
98	Ordered arrays of bottom-up III-nitride core-shell nanostructures. , 2015, , .		6
99	Controllable finite ultra-narrow quality-factor peak in a perturbed Dirac-cone band structure of a photonic-crystal slab. Applied Physics Letters, 2021, 119, .	1.5	6
100	Comparison of a Sleep Quality Index between Normal and Obstructive Sleep Apnea Patients. , 2005, 2005, 1154-7.		5
101	Arsenic-induced etched nanovoids on GaSb (100). Journal of Applied Physics, 2007, 102, 044312.	1.1	5
102	A cognitive radio antenna design based on optically pumped reconfigurable antenna system (OPRAS). , 2011, , .		5
103	Measuring the transition switching speed of a semiconductor-based photoconductive switch using RF techniques. , 2011, , .		5
104	Low homologous temperature (<0.2) sputtering of indium films on silicon. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 060602.	0.6	5
105	Carrier dynamics and photoluminescence quenching mechanism of strained InGaSb/AlGaSb quantum wells. Journal of Applied Physics, 2013, 113, 053505.	1.1	5
106	MEMST. , 2015, , .		5
107	Experimental Evidence of Suppression of Subterahertz Phonons and Thermal Conductivity in GaAs/AlAs Superlattices Due to Extrinsic Scattering Processes. Journal of Physical Chemistry C, 2018, 122, 29577-29585.	1.5	5
108	Carrier concentration and transport in Be-doped InAsSb for infrared sensing applications. Infrared Physics and Technology, 2019, 96, 184-191.	1.3	5

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109	Influence of quantum dot morphology on the optical properties of GaSb/GaAs multilayers. Applied Physics Letters, 2020, 116, .	1.5	5
110	Mid-infrared interband cascade light emitting devices grown on off-axis silicon substrates. Optics Express, 2021, 29, 35426.	1.7	5
111	Study of Al ₂ O ₃ /ZrO ₂ (5 nm/20nm) Nanolaminate Composite. Composites Research, 2013, 26, 60-65.	0.1	5
112	Maintaining atomically smooth GaAs surfaces after high-temperature processing for precise interdiffusion analysis and materials engineering. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2021, 39, .	0.6	5
113	Photoluminescence and minority carrier lifetime of quinary GaInAsSbBi grown on GaSb by molecular beam epitaxy. Applied Physics Letters, 2022, 120, .	1.5	5
114	GaN epitaxy on Cu(110) by metal organic chemical vapor deposition. Applied Physics Letters, 2012, 100, .	1.5	4
115	Intracavity laser cooling using a VECSEL. , 2012, , .		4
116	Growth and Optimization of 2-Î¼m InGaSb/AlGaSb Quantum-Well-Based VECSELs on GaAs/AlGaAs DBRs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1700611-1700611.	1.9	4
117	Isolating GaSb Membranes Grown Metamorphically on GaAs Substrates Using Highly Selective Substrate Removal Etch Processes. Journal of Electronic Materials, 2015, 44, 1327-1331.	1.0	4
118	Development of thin film metamorphic GaSb cells by epitaxial lift-off from GaAs substrates. , 2016, , .		4
119	Revealing Temperature-Dependent Absorption and Emission Enhancement Factors in Plasmon Coupled Semiconductor Heterostructures. ACS Applied Electronic Materials, 2019, 1, 1439-1448.	2.0	4
120	Modeling Misfit Dislocation Arrays for the Growth of Low-Defect Density AlSb on Si. Materials Research Society Symposia Proceedings, 2006, 934, 1.	0.1	3
121	Device Characteristics of GaInSb/AlGaSb Quantum Well Lasers Monolithically Grown on GaAs Substrates by Using an Interfacial Misfit Array. Journal of Electronic Materials, 2008, 37, 1758-1763.	1.0	3
122	Electrical and structural characterization of a single GaSb•InAs•GaSb quantum well grown on GaAs using interface misfit dislocations. Journal of Applied Physics, 2008, 104, .	1.1	3
123	Characterization of Interfacial Misfit Array Formation for GaSb Growth on GaAs by Transmission Electron Microscopy. Microscopy and Microanalysis, 2009, 15, 1062-1063.	0.2	3
124	High-power 1.25 Å, Åµm InAs QD VECSEL based on resonant periodic gain structure. Proceedings of SPIE, 2011, , .	0.8	3
125	Lattice mismatched growth for mid-IR VECSELs. Proceedings of SPIE, 2011, , .	0.8	3
126	Power scaling of cw and pulsed IR and mid-IR OPSLs. , 2011, , .		3

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127	TEM based analysis of III-Sb VECSELs on GaAs substrates for improved laser performance.. Proceedings of SPIE, 2013, , .	0.8	3
128	Beryllium implant activation and damage recovery study in n-type GaSb. , 2014, , .		3
129	Low resistance palladium/molybdenum based ohmic contacts to n-GaSb grown on GaAs. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 04E108.	0.6	3
130	Characterization of carrier transport properties in strained crystalline Si wall-like structures in the quasi-quantum regime. Journal of Applied Physics, 2015, 118, 134301.	1.1	3
131	Thin-Film Gallium Antimonide for Room-Temperature Radiation Detection. Journal of Electronic Materials, 2015, 44, 3288-3293.	1.0	3
132	GaSb thermophotovoltaics: current challenges and solutions. Proceedings of SPIE, 2015, , .	0.8	3
133	Pixelated GaSb solar cells on silicon by membrane bonding. Applied Physics Letters, 2018, 113, 123502.	1.5	3
134	InGaSb Defect Filter Layer to Improve Performance of GaSb Solar Cells Grown on GaAs Substrates. Journal of Electronic Materials, 2020, 49, 7153-7158.	1.0	3
135	Imaging of surface acoustic waves on GaAs using 2D confocal Raman microscopy and atomic force microscopy. Applied Physics Letters, 2021, 118, .	1.5	3
136	1.55 μm GaSb/AlGaSb MQW diode lasers grown on GaAs substrates using interfacial misfit (IMF) arrays. , 2007, , .		2
137	Fabrication and characterization of metal-oxide-semiconductor GaAs capacitors on Ge \times Si \times Ge \times Si substrates with Al \times O \times gate dielectric. Journal of Vacuum Science & Technology B, 2008, 26, 1182.	1.3	2
138	Characterization of thin GaAs films grown on nanostructured silicon substrates. , 2010, , .		2
139	Ultra-low resistance NiGeAu and PdGeAu ohmic contacts on N-GaSb grown on GaAs. , 2013, , .		2
140	Time-resolved photo and radio-luminescence studies demonstrate the possibility of using InGaN/GaN quantum wells as fast scintillators. Nanotechnology, 2015, 26, 090501.	1.3	2
141	3 μm thick GaSb membrane diodes integrated with CVD diamond heat spreaders for thermally managed TPV cells. , 2015, , .		2
142	Accurate Cloning of the Memory Access Behavior. IPSJ Transactions on System LSI Design Methodology, 2016, 9, 49-60.	0.5	2
143	Optically Pumped 1 μm Low Threshold Photonic Crystal Surface Emitting Lasers Grown on GaAs Substrate. , 2019, , .		2
144	A transmission electron microscopy study of dislocation propagation and filtering in highly mismatched GaSb/GaAs heteroepitaxy. Journal of Applied Physics, 2020, 128, 225301.	1.1	2

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145	Submonolayer Quantum-Dot Based Saturable Absorber for Femtosecond Pulse Generation. Journal of Electronic Materials, 2021, 50, 2710-2715.	1.0	2
146	Degradation mechanism of SESAMs under intense ultrashort pulses in modelocked VECSELS. , 2018, , .		2
147	Monolithically integrated III-Sb based laser diodes grown on miscut Si substrates. , 2008, , .		1
148	Perforated (In)GaSb quantum wells on GaSb substrates through the use of As ₂ based in situ etches. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 041204.	0.6	1
149	Polarization Properties of GaN Nanowire Lasers. , 2013, , .		1
150	Selective-Area Growth of III-Nitride Core-Shell Nanowalls for Light-Emitting and Laser Diodes. , 2014, , .		1
151	Investigation of Surface Defects in AlInSb Metamorphic Buffer (MB) Grown on GaSb. Journal of Electronic Materials, 2016, 45, 6258-6264.	1.0	1
152	Recent advances in high power microwave sources and the science of electronics in extreme electromagnetic environments at the university of new mexico. , 2017, , .		1
153	InP-based multiple type-II quantum-well integrated waveguide p-i-n photodiodes for mid-infrared detection. , 2017, , .		1
154	Comparison of carrier localization effects between InAs quantum dashes and quantum dots in a DWELL (dashes- or dots-in-a-well) configuration. Physica E: Low-Dimensional Systems and Nanostructures, 2020, 124, 114376.	1.3	1
155	Fabrication of Photonic Crystal Surface Emitting Lasers (PCSELS) by Epitaxial Regrowth. , 2021, , .		1
156	Tailoring Second Harmonic Diffraction in GaAs Metasurfaces via Crystal Orientation. , 2019, , .		1
157	Time Resolved Holography Scheme Using a Table Top Soft X-Ray Laser. Springer Proceedings in Physics, 2014, , 165-170.	0.1	1
158	Enhanced Optical Nonlinearities in All-Dielectric Metasurfaces. , 2019, , .		1
159	Temperature dependent absorption and emission enhancement factors in plasmon coupled semiconductor heterostructures. , 2019, , .		1
160	Monolithic integration of Sb-based photopumped lasers on Si. , 0, , .		0
161	Optical Properties of Stranski-Krastanow and Strain-Free GaSb Quantum Dots on GaAs Substrates - Towards Sb-based Type-II Quantum Dot Emitters -. , 2006, , .		0
162	Optical Properties of Stranski-Krastanow and Strain-Free GaSb Quantum Dots on GaAs Substrates - Towards Sb-based Type-II Quantum Dot Emitters -. , 0, , .		0

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163	GaSb QW-based 'buffer-free' vertical LED monolithically embedded within a GaAs cavity using interfacial misfit arrays. , 2006, , .		0
164	Room Temperature InGaSb Quantum Well Microcylinder Lasers at 2 μ m Grown Monolithically on a Silicon Substrate. , 2006, , .		0
165	Monolithically Integrated III-Sb Superluminescent Light Emitting Diodes on Si (100) Substrates. , 2007, , .		0
166	Monolithically integrated III-Sb diode lasers on Si using interfacial misfit arrays. , 2007, , .		0
167	Type II Strain Layer Superlattices (SLS's) grown on GaAs Substrates. Conference Proceedings - Lasers and Electro-Optics Society Annual Meeting-LEOS, 2007, , .	0.0	0
168	1.65 μ m buffer-free GaSb/AlGaSb quantum-well diode lasers grown on a GaAs substrate operating at room temperature. Device Research Conference, IEEE Annual, 2007, , .	0.0	0
169	TEM Characterization of GaSb Growth on GaAs (001) Substrate: Growth Mode and Defect Evaluation. Microscopy and Microanalysis, 2010, 16, 1516-1517.	0.2	0
170	Transmission electron microscopy study of metamorphic III-Sb VECSELs on GaAs/AlGaAs distributed Bragg reflectors. , 2012, , .		0
171	Investigation of InAs quantum dashes for 1.45-2.1 μ m vertical external cavity surface emitting laser active regions. Proceedings of SPIE, 2013, , .	0.8	0
172	Isolation and characterization of large-area GaSb membranes grown on GaAs substrates. , 2013, , .		0
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